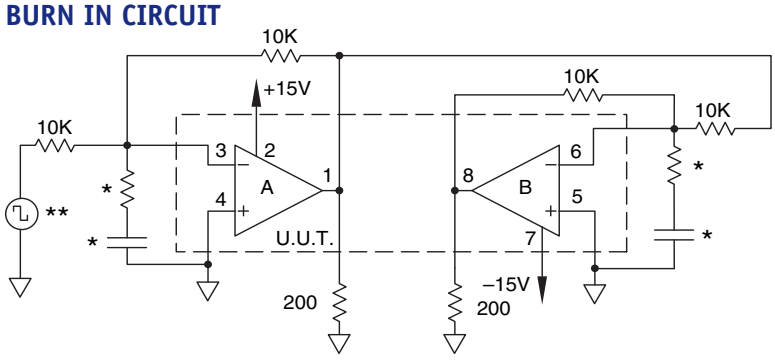
| SG | PARAMETER | SYMBOL | TEMP. | POWER | TEST CONDITIONS | MIN | MAX | UNITS |
|---|---|---|---|---|---|---|---|---|
| 1 | Quiesent Current | $I_Q$ | 25°C | ±15 | $V_{IN}$ = 0, $A_V$ = 100 | | 30 | mA |
| 1 | Input Offset Voltage | $V_{OS}$ | 25°C | ±2.5 | $V_{IN}$ = 0, $A_V$ = 100 | | 10 | mV |
| 1 | Input Offset Voltage | $V_{OS}$ | 25°C | ±15 | $V_{IN}$ = 0, $A_V$ = 100 | | 10 | mV |
| 1 | Input Offset Voltage | $V_{OS}$ | 25°C | ±20 | $V_{IN}$ = 0, $A_V$ = 100 | | 14 | mV |
| 1 | Input Bias Current + IN | $+I_B$ | 25°C | ±15 | $V_{IN}$ = 0 | | 1000 | nA |
| 1 | Input Bias Current –IN | $-I_B$ | 25°C | ±15 | $V_{IN}$ = 0 | | 1000 | nA |
| 1 | Input Offset Current | $I_{OS}$ | 25°C | ±15 | $V_{IN}$ = 0 | | 500 | nA |
| 3 | Quiesent Current | $I_Q$ | –55°C | ±15 | $V_{IN}$ = 0, $A_V$ = 100 | | 30 | mA |
| 3 | Input Offset Voltage | $V_{OS}$ | –55°C | ±2.5 | $V_{IN}$ = 0, $A_V$ = 100 | | 14 | mV |
| 3 | Input Offset Voltage | $V_{OS}$ | –55°C | ±15 | $V_{IN}$ = 0, $A_V$ = 100 | | 14 | mV |
| 3 | Input Offset Voltage | $V_{OS}$ | –55°C | ±20 | $V_{IN}$ = 0, $A_V$ = 100 | | 18 | mV |
| 3 | Input Bias Current + IN | $+I_B$ | –55°C | ±15 | $V_{IN}$ = 0 | | 1000 | nA |
| 3 | Input Bias Current –IN | $-I_B$ | –55°C | ±15 | $V_{IN}$ = 0 | | 1000 | nA |
| 3 | Input Offset Current | $I_{OS}$ | –55°C | ±15 | $V_{IN}$ = 0 | | 500 | nA |
| 2 | Quiesent Current | $I_Q$ | 125°C | ±15 | $V_{IN}$ = 0, $A_V$ = 100 | | 40 | mA |
| 2 | Input Offset Voltage | $V_{OS}$ | 125°C | ±2.5 | $V_{IN}$ = 0, $A_V$ = 100 | | 15 | mV |
| 2 | Input Offset Voltage | $V_{OS}$ | 125°C | ±15 | $V_{IN}$ = 0, $A_V$ = 100 | | 15 | mV |
| 2 | Input Offset Voltage | $V_{OS}$ | 125°C | ±20 | $V_{IN}$ = 0, $A_V$ = 100 | | 19 | mV |
| 2 | Input Bias Current + IN | $+I_B$ | 125°C | ±15 | $V_{IN}$ = 0 | | 1000 | nA |
| 2 | Input Bias Current –IN | $-I_B$ | 125°C | ±15 | $V_{IN}$ = 0 | | 1000 | nA |
| 2 | Input Offset Current | $I_{OS}$ | 125°C | ±15 | $V_{IN}$ = 0 | | 500 | nA |
| 4 | Output Voltage $I_O$= 2A | $V_O$ | 25°C | ±9.5 | $R_L$ = 3Ω | 6.0 | | V |
| 4 | Output Voltage $I_O$= 100mA | $V_O$ | 25°C | ±11 | $R_L$ = 100Ω | 9.9 | | V |
| 4 | Output Voltage $I_O$= 1A | $V_O$ | 25°C | ±4.8 | $R_L$ = 3Ω | 2.8 | | V |
| 4 | Stability/Noise | $E_N$ | 25°C | ±15 | $R_L$ = 500Ω, $A_V$ = 1 $C_L$ = 1.5nF | | 1.0 | mV |
| 4 | Crosstalk | XTLK | 25°C | ±15 | $R_L$ = 3Ω | 50 | | dB |
| 4 | Slew Rate | SR | 25°C | ±15 | $R_L$ = 500Ω | .5 | | V/µS |
| 4 | Open Loop Gain | $A_{OL}$ | 25°C | ±15 | $R_L$ = 500Ω, F =10Hz | 75 | | dB |
| 4 | Common-mode Rejection | CMR | 25°C | ±17 | $R_L$ = 500Ω, $V_{CM}$ = ±14V | 60 | | dB |
| 6 | Output Voltage $I_O$= 2A | $V_O$ | –55°C | ±9.5 | $R_L$ = 3Ω | 6.0 | | V |
| 6 | Output Voltage $I_O$= 100mA | $V_O$ | –55°C | ±11 | $R_L$ = 100Ω | 9.9 | | V |
| 6 | Output Voltage $I_O$= 1A | $V_O$ | –55°C | ±4.8 | $R_L$ = 3Ω | 2.8 | | V |
| 6 | Stability/Noise | $E_N$ | –55°C | ±15 | $R_L$ = 500Ω, $A_V$ = 1, $C_L$ = 1.5nF | | 1.0 | mV |
| 6 | Slew Rate | SR | –55°C | ±15 | $R_L$ = 500Ω | .5 | | V/µS |
| 6 | Open Loop Gain | $A_{OL}$ | –55°C | ±15 | $R_L$ = 500Ω, F = 10Hz | 75 | | dB |
| 6 | Common-mode Rejection | CMR | –55°C | ±17 | $R_L$ = 500Ω, $V_{CM}$ = ±14V | 60 | | dB |
| 5 | Output Voltage $I_O$= 1A | $V_O$ | 125°C | ±4.8 | $R_L$ = 3Ω | 2.8 | | V |
| 5 | Output Voltage $I_O$= 100mA | $V_O$ | 125°C | ±11 | $R_L$ = 100Ω | 9.9 | | V |
| 5 | Output Voltage $I_O$= 750mA | $V_O$ | 125°C | ±4.0 | $R_L$ = 3Ω | 2.25 | | V |
| 5 | Stability/Noise | $E_N$ | 125°C | ±15 | $R_L$ = 500Ω, $A_V$ = 1, $C_L$ = 1.5nF | | 1.0 | mV |
| 5 | Slew Rate | SR | 125°C | ±15 | $R_L$ = 500Ω | .5 | | V/µS |
| 5 | Open Loop Gain | $A_{OL}$ | 125°C | ±15 | $R_L$ = 500Ω, F = 10Hz | 75 | | dB |
| 5 | Common-mode Rejection | CMR | 125°C | ±17 | $R_L$ = 500Ω, $V_{CM}$ = ±14V | 60 | | dB |

## BURN IN CIRCUIT




* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.